

ABSTRACT

A method of processing a substrate according to the present invention, the method including a preparation step of preparing
5 a substrate having a first surface including silicon nitride;
and a surface modification step of forming a protective film
that protects the first surface, in which the surface
modification step includes a gas exposure treatment in which the
first surface in a heated state is brought into contact with a
10 modification gas containing gas of a surface modifier in a
substrate holding space, and the surface modifier has a
predetermined silyl ester of a carboxylic acid.

FIG.1